

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1 – 6. (Cancelled)

7. (Previously Presented) A method comprising:

supplying an initial substrate comprising an SiC support bearing a layer of SiO<sub>2</sub> whereon a thin layer of SiC is transferred, the thin layer of SiC being a 6H or 4H polytype SiC; and  
conducting an epitaxy of SiC on the thin layer of SiC at a temperature from 1450°C to 1550°C to obtain 6H or 4H polytype epitaxy on the transferred thin 6H or 4H polytype layer respectively.

8. (Previously Presented) The method according to claim 7, wherein before the epitaxy step, an initial substrate preparation step is provided to improve the surface quality of the transferred thin SiC layer.

9. (Previously Presented) The method according to claim 8, wherein the preparation step consists of subjecting the surface of the transferred thin SiC layer to an operation selected from polishing etching and hydrogen etching.

10. (Previously Presented) The method according to claim 7, wherein several SiC layers are successively grown epitaxially on the thin SiC layer.

11. (Previously Presented) A semiconductor device produced on an SiCOI composite substrate obtained by means of the manufacturing method according to any of claims 7 to 10.

12 – 26. (Cancelled)